BCX56-10R1

Preferred Device

NPN Silicon Epitaxial Transistor

These NPN Silicon Epitaxial transistors are designed for use in audio amplifier applications. The device is housed in the SOT-89 package, which is designed for medium power surface mount applications.

• High Current: 1.0 Amp

• Available in 7 inch/1000 unit Tape and Reel

• Device Marking: BK

MAXIMUM RATINGS ($T_C = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	80	Vdc
Collector-Base Voltage	V _{CBO}	100	Vdc
Emitter-Base Voltage	V _{EBO}	5	Vdc
Collector Current	IC	1	Adc
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D (Note 1.) (Note 2.)	1.56 13 0.67 5.0	Watts mW/°C Watts mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-65 to 150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction-to-Ambient (surface mounted)	R _θ JA (Note 1.) (Note 2.)	80 190	°C/W
Maximum Temperature for Soldering Purposes Time in Solder Bath	TL	260 10	°C Sec

1. FR-4 @ 1.0 X 1.0 inch Pad

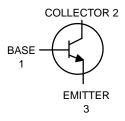
2. FR-4 @ Minimum Pad



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http://onsemi.com

MEDIUM POWER
NPN SILICON
HIGH CURRENT
TRANSISTOR
SURFACE MOUNT





SOT-89 CASE 1213 STYLE 2



MARKING DIAGRAM

Y = Year CodeM = Month CodeBK = Device Code

ORDERING INFORMATION

Device	Package	Shipping		
BCX56-10R1	SOT-89	1000/Tape & Reel		

Preferred devices are recommended choices for future use and best overall value.

BCX56-10R1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristics	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•		•
Collector-Base Breakdown Voltage (I _C = 100 μAdc, I _E = 0)	V(BR)CBO	100	_	_	Vdc
Collector-Emitter Breakdown Voltage (I _C = 1.0 mAdc, I _B = 0)	V(BR)CEO	80	_	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	V(BR)EBO	5.0	_	-	Vdc
Collector-Base Cutoff Current (V _{CB} = 30 Vdc, I _E = 0)	ICBO	_	_	100	nAdc
Emitter-Base Cutoff Current (V _{EB} = 5.0 Vdc, I _C = 0)	I _{EBO}	_	_	10	μAdc
ON CHARACTERISTICS (Note 3.)					
DC Current Gain (I _C = 5.0 mA, V _{CE} = 2.0 V) (I _C = 150 mA, V _{CE} = 2.0 V) (I _C = 500 mA, V _{CE} = 2.0 V)	hFE	25 63 25	- - -	_ 160 _	-
Collector-Emitter Saturation Voltage (I _C = 500 mAdc, I _B = 50 mAdc)	VCE(sat)	-	_	0.5	Vdc
Base-Emitter On Voltage (I _C = 500 mAdc, V _{CE} = 2.0 Vdc)	V _{BE} (on)	-	-	1.0	Vdc
DYNAMIC CHARACTERISTICS					
Current-Gain – Bandwidth Product (I _C = 10 mAdc, V _{CE} = 5.0 Vdc, f = 35 MHz)	fT	_	130	-	MHz

^{3.} Pulse Test: Pulse Width $\leq 300~\mu s,~Duty~Cycle \leq 2.0\%$

TYPICAL ELECTRICAL CHARACTERISTICS

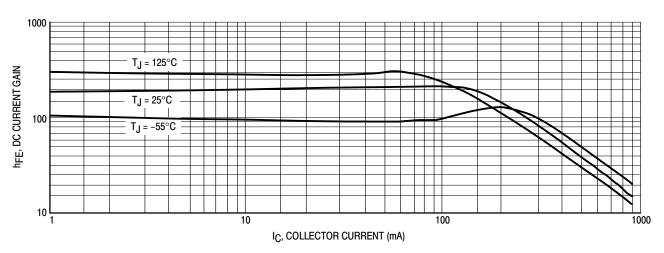
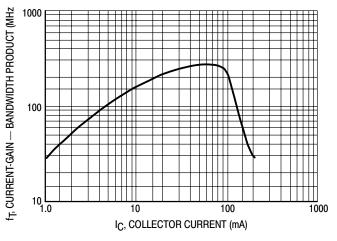


Figure 1. DC Current Gain

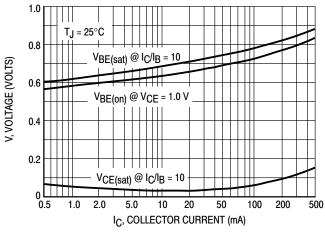
TYPICAL ELECTRICAL CHARACTERISTICS



80 60 40 40 Cibo T_J = 25°C Cibo 8.0 6.0 4.0 0.1 0.2 0.5 1.0 2.0 5.0 10 20 50 100 V_R, REVERSE VOLTAGE (VOLTS)

Figure 2. Current-Gain - Bandwidth Product

Figure 3. Capacitance



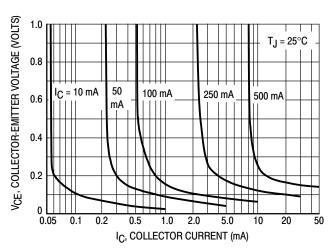


Figure 4. "On" Voltages

Figure 5. Collector Saturation Region

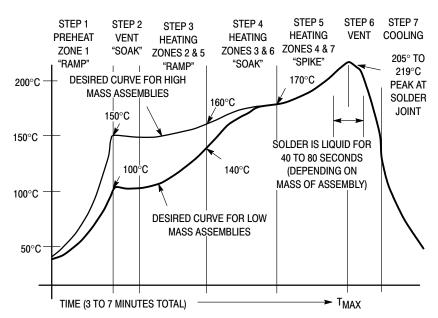
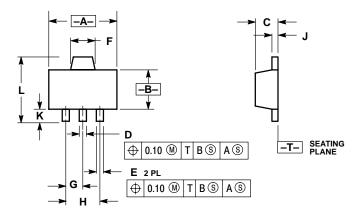


Figure 6. Typical Solder Heating Profile

BCX56-10R1

PACKAGE DIMENSIONS

SOT-89 (3-LEAD) CASE 1213-02 ISSUE C



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 Y14 5M 1982
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. 1213-01 OBSOLETE, NEW STANDARD 1213-02.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.40	4.60	0.173	0.181
В	2.40	2.60	0.094	0.102
С	1.40	1.60	0.055	0.063
D	0.37	0.57	0.015	0.022
Е	0.32	0.52	0.013	0.020
F	1.50	1.83	0.059	0.072
G	1.50 BSC		0.059 BSC	
Н	3.00 BSC		0.118 BSC	
J	0.30	0.50	0.012	0.020
K	0.80		0.031	
Г		4.25		0.167

STYLE 2: PIN 1. BASE 2. COLLECTOR 3. EMITTER

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